ABSTRACT OF THE DISCLOSURE

POLISHING METHOD AND POLISHING APPARATUS

A polishing method capable of terminating polishing of a substrate, such as a wafer, at a preset polishing time is disclosed. The polishing method includes: polishing a substrate by pressing the substrate against a polishing surface of a polishing pad, while regulating a temperature of the polishing surface by a heat exchanger; calculating a target polishing rate required for an actual polishing time to coincide with a target polishing time, the actual polishing time being a time duration from start of polishing the substrate until a film thickness of the substrate reaches a target thickness; determining a target temperature of the polishing surface that can achieve the target polishing rate; and during polishing of the substrate, changing a temperature of the polishing surface to the target temperature by the heat exchanger.

FIG. 1